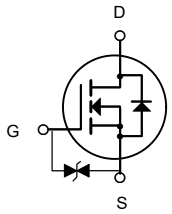
Description

The AO3420 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

SOT-23-3L



N-Channel MOSFET

General Features

V_{DS} = 20V I_D =6.5A

$R_{DS(ON)}$ < 22mΩ @ V_{GS}=4. 5V

ESD=2500HBM

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AO3420	SOT-23-3L	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	±12	V
I_D	Drain Current-Continuous	6.5	A
I_{DM}	Drain Current-Pulsed (Note 1)	30	A
P_D	Maximum Power Dissipation	1.4	W
T_J,T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃
$R_{\theta JA}$	Thermal Resistance,Junction-to-Ambient (Note 2)	89	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=250μA	20		-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V,V_{GS}=0V	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±10V,V_{DS}=0V	-	-	±10	μA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.45	0.7	1.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=6.5A	-	14	22	mΩ
		V_{GS}=2.5V, I_D=5.5A	-	17	26	mΩ
		V_{GS}=1.8V, I_D=5A	-	28	40	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=6.5A	8	-	-	S
Input Capacitance	C_{lss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz	-	660	-	PF
Output Capacitance	C_{oss}		-	160	-	PF
Reverse Transfer Capacitance	C_{rss}		-	87	-	PF
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,R_L=1. 5Ω V_{GS}=5V,R_{GEN}=3Ω	-	0.5		nS
Turn-on Rise Time	t_r		-	1		nS
Turn-Off Delay Time	$t_{d(off)}$		-	12		nS
Turn-Off Fall Time	t_f		-	4		nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=6.5A, V_{GS}=4.5V	-	8		nC
Gate-Source Charge	Q_{gs}		-	2.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3	-	nC
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=6.5A	-	-	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	6.5	A

Notes:

Repetitive Rating: Pulse width limited by maximum junction temperature.
Surface Mounted on FR4 Board, t ≤ 10 sec.
Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
Guaranteed by design, not subject to production

Typical Characteristics

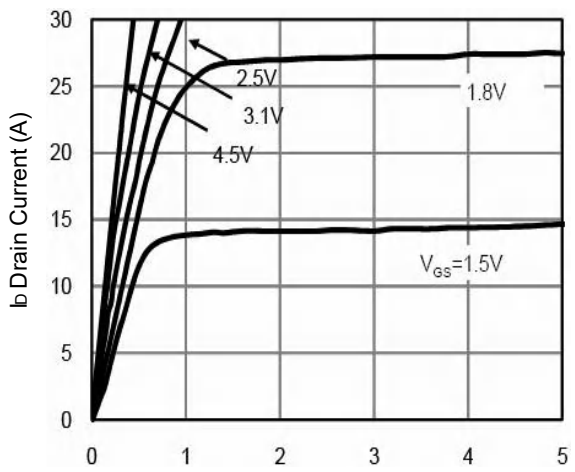


Fig.1 Typical Output Characteristics

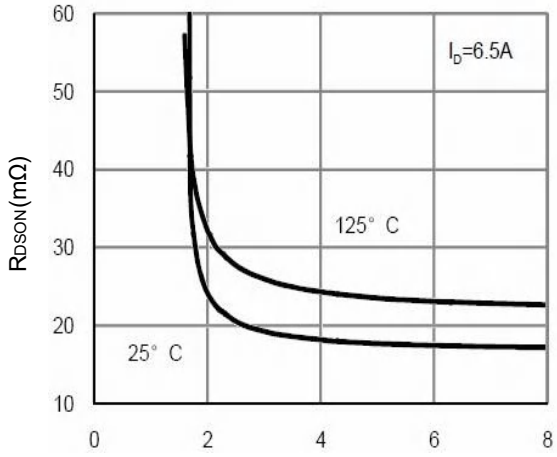


Fig.2 On-Resistance vs. Gate-Source

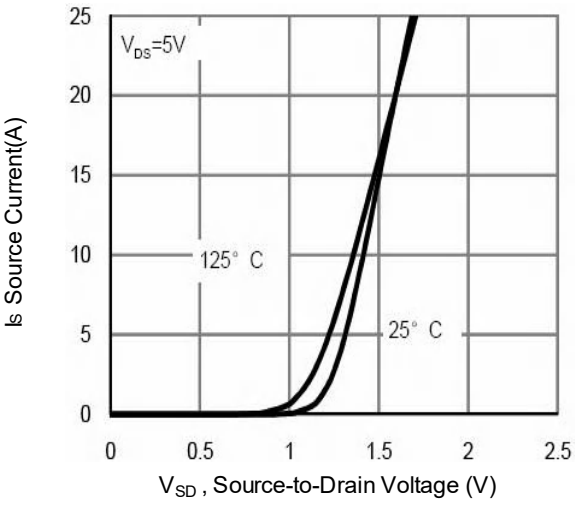


Fig.3 Forward Characteristics of Reverse

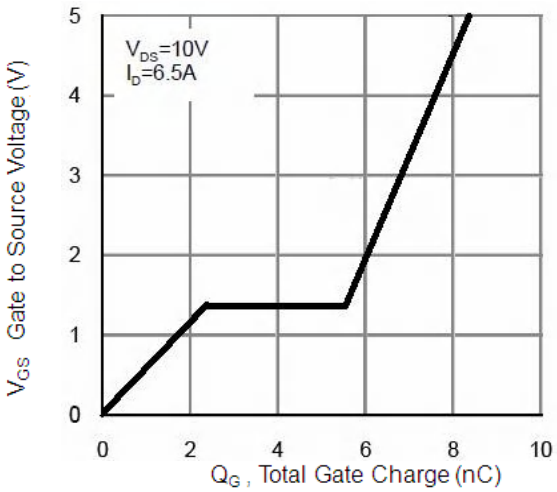


Fig.4 Gate-Charge Characteristics

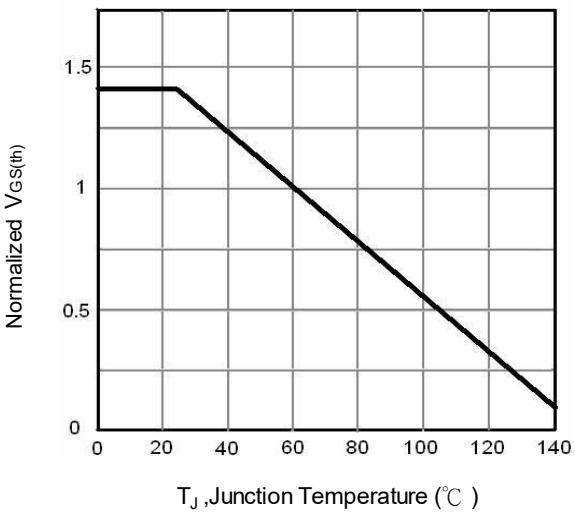


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

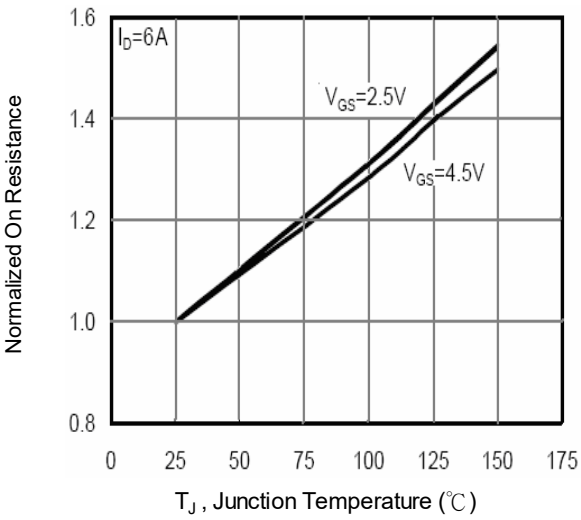


Fig.6 Normalized R_{DSON} vs. T_J

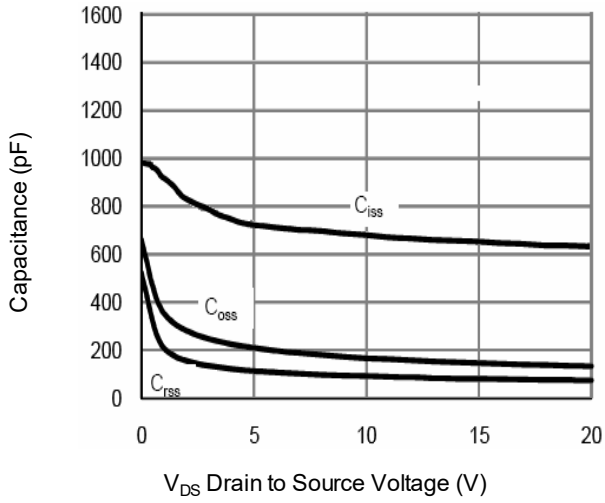


Fig.7 Capacitance

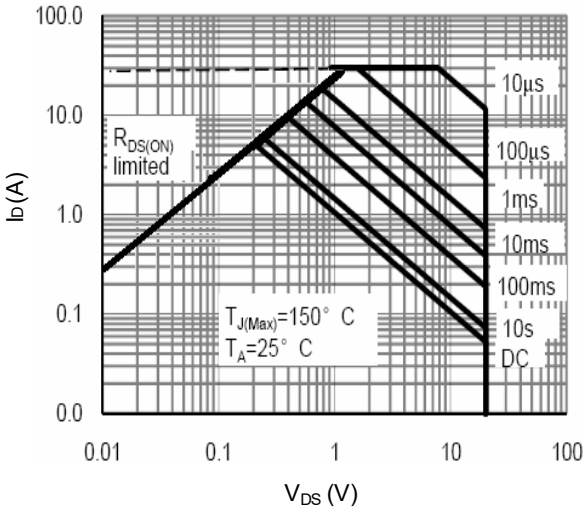


Fig.8 Safe Operating Area

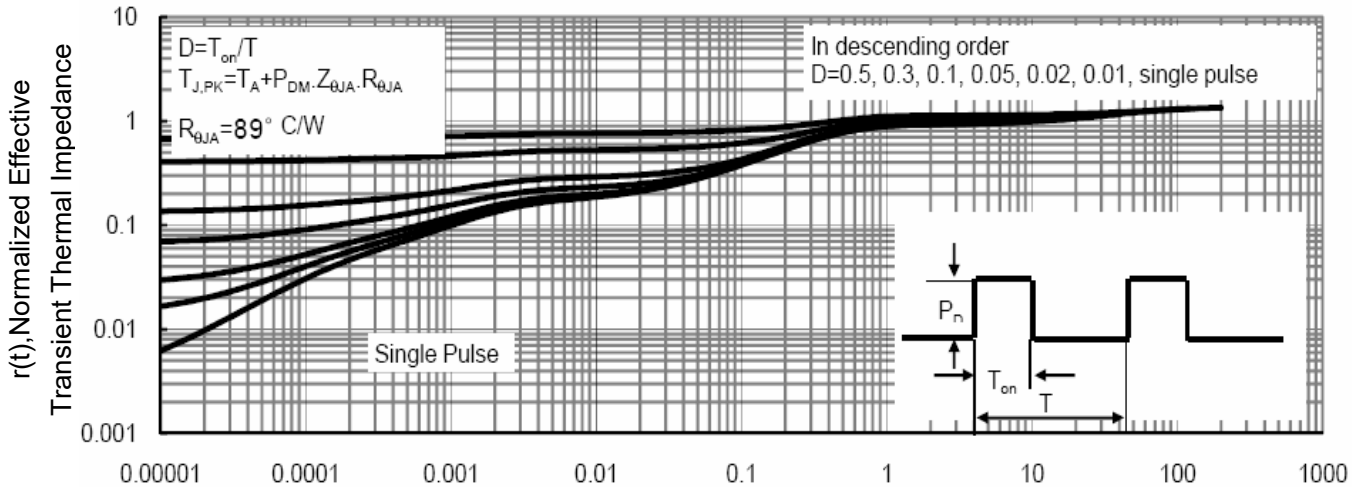


Fig.9 Normalized Maximum Transient Thermal Impedance

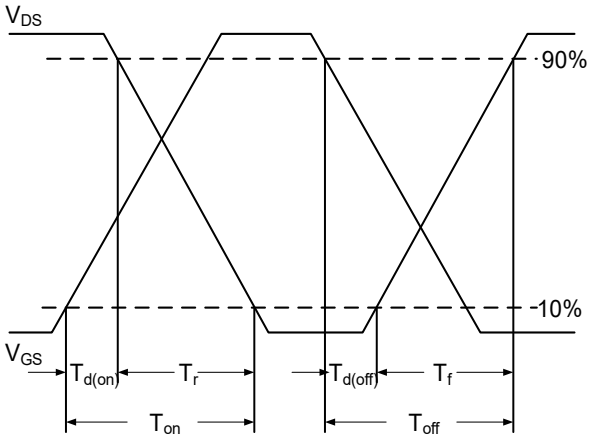


Fig.10 Switching Time Waveform

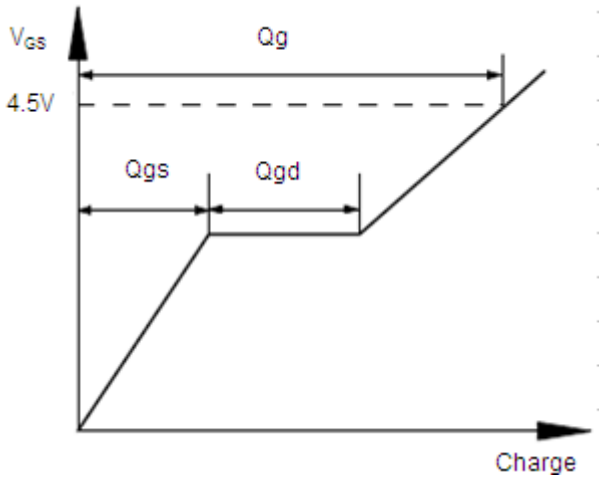
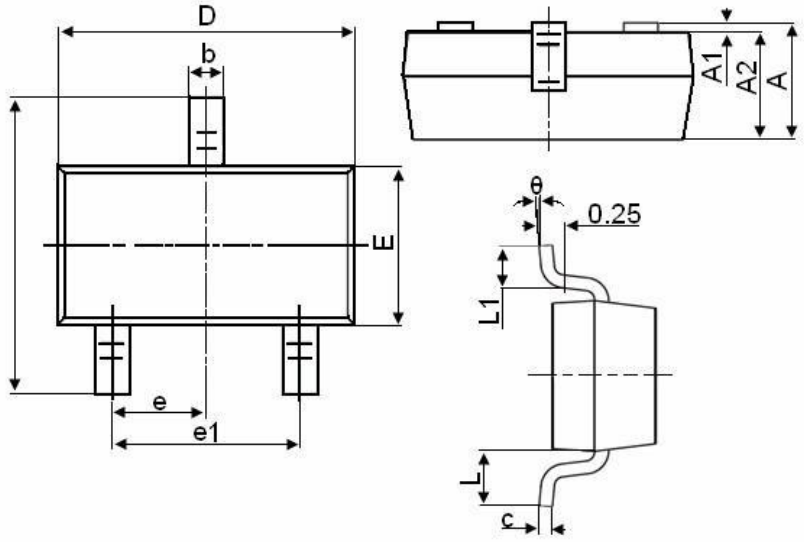


Fig.11 Gate Charge Waveform

SOT-23- 3L Package Information



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
θ	0°	8°

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